

In the Claims

Claims 1-39 (Canceled).

40. (Currently Amended): A wafer bonding method of forming ~~silicon-on-insulator comprising~~ silicon-on-insulator-comprising integrated circuitry, comprising:

forming silicon dioxide on at least a portion of an outer surface of a handle wafer;

nitridizing at least a portion of an outer surface of the silicon dioxide effective to form silicon nitride on silicon dioxide;

after the nitridizing, joining the handle wafer with an outer surface of a device wafer;

forming a pair of source/drain regions separated by a channel region within the silicon, the silicon nitride being received intermediate the source/drain regions and the silicon dioxide; and

forming a field effect transistor gate operably proximate the channel region.

41. (Original): The method of claim 40 wherein the outer surface of the device wafer to which the handle wafer is joined comprises crystalline silicon.

42. (Original): The method of claim 40 wherein the outer surface of the device wafer to which the handle wafer is joined comprises silicon nitride.

43. (Original): The method of claim 40 wherein the outer surface of the device wafer to which the handle wafer is joined comprises silicon dioxide.

44. (Original): The method of claim 40 wherein the nitridizing comprises ion implanting.

45. (Original): The method of claim 40 wherein the nitridizing comprises direct plasma nitridation.

46. (Original): The method of claim 40 wherein the nitridizing comprises remote plasma nitridation.

47. (Original): The method of claim 40 wherein the nitridizing comprises chemical vapor deposition.

48. (Currently Amended): The method of claim 40 wherein the nitridation is void of either direct or remote ~~nitride-containing~~ nitride-containing plasma exposure.

Claims 49-61 (Cancelled).

62. (Previously Presented): The method of claim 40 wherein the nitridizing comprises N_2 .

63. (Previously Presented): The method of claim 40 wherein the nitridizing comprises NO_x .

64. (Previously Presented): The method of claim 40 wherein the nitridizing comprises NH_3 .

65. (Previously Presented): The method of claim 40 wherein the nitridizing comprises N_2O .

66. (Previously Presented): The method of claim 40 wherein the silicon nitride is from about 5 Angstroms to about 50 Angstroms thick.